TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE POWER GaAs FET

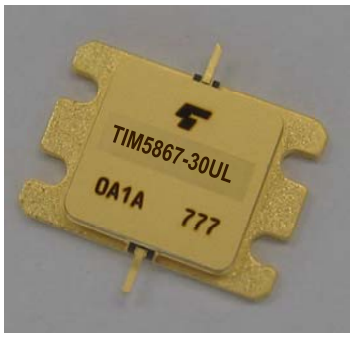
TIM5867-30UL

FEATURES

- BROAD BAND INTERNALLY MATCHED FET
- HIGH POWER

  P1dB= 45.0dBm at 5.85GHz to 6.75GHz
- HIGH GAIN

  G1dB= 10.0dB at 5.85GHz to 6.75GHz
- HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 6.4A f = 5.85 to 6.75GHz	dBm	44.0	45.0	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	9.0	10.0	—
Drain Current	IDS1		A	—	7.0	8.0
Gain Flatness	ΔG		dB	—	—	±0.8
Power Added Efficiency	ηadd		%	—	41	—
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po= 34.0dBm, Δf= 5MHz (Single Carrier Level)	dBc	-44	-47	—
Drain Current	IDS2		A	—	7.0	8.0
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C	—	—	100

Recommended Gate Resistance(Rg): 28 Ω

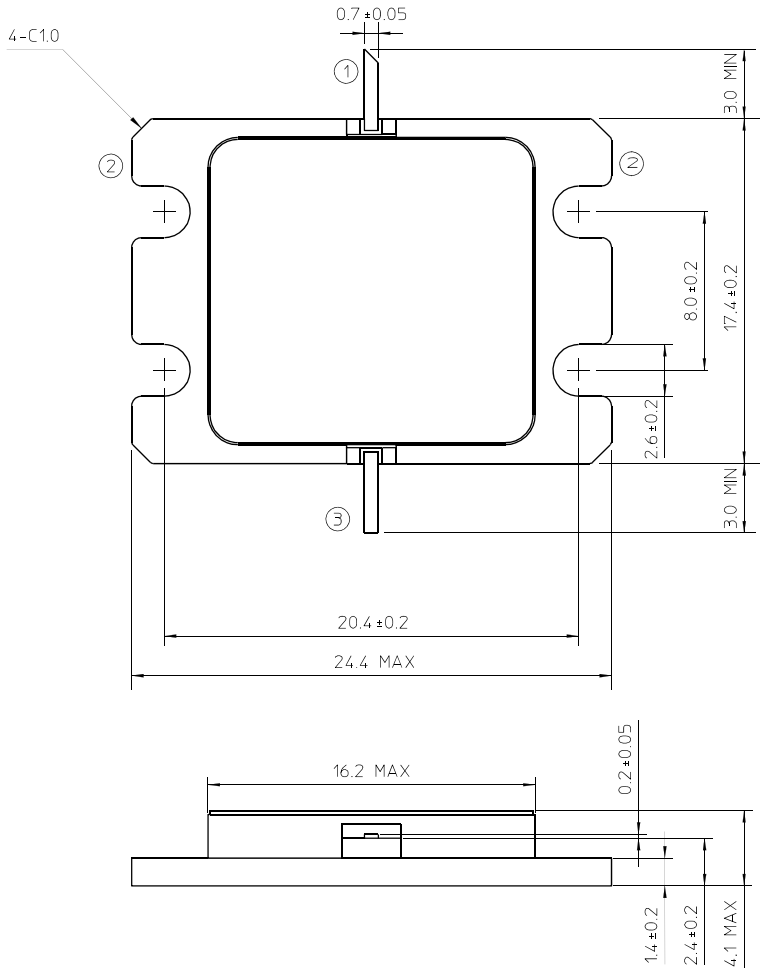
ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 10.0A	S	—	8.0	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 80mA	V	-0.5	-2.0	-3.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	16.0	—
Gate-Source Breakdown Voltage	VGSO	IGS= -240μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	1.0	1.5

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	18.0
Total Power Dissipation (Tc= 25°C)	PT	W	100
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7-AA05A)



Unit in mm

① Gate
② Source
③ Drain

HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.